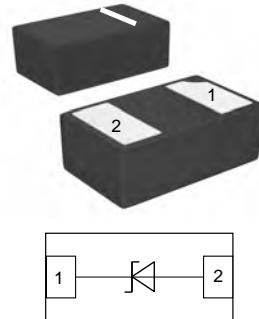


## Features

- 1500 Watts peak pulse power ( $T_p = 8/20\mu s$ )
- DFN1610-2 package
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Normal capacitance ( $C_j=70pF$ )
- Protection one data/power line to:  
 IEC 61000-4-2 ±30kV contact ±30kV air  
 IEC 61000-4-4 (EFT) 40A (5/50ns)  
 IEC 61000-4-5 (Lightning) 52A (8/20μs)



## Mechanical Data

- **Case:** DFN1610-2 (plastic package)  
 Lead free; RoHS compliant; Halogen free
- **Molding Compound Flammability Rating:**  
 UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:  
 260 °C/10 sec. at terminals

## Applications

- Charger Protection
- Parallel & Serial Port Protection
- Personal Digital Assistant (PDA)
- Microcontroller Input Protection
- Cellular Phones
- I<sup>2</sup>C Bus Protection

## Absolute Maximum Ratings

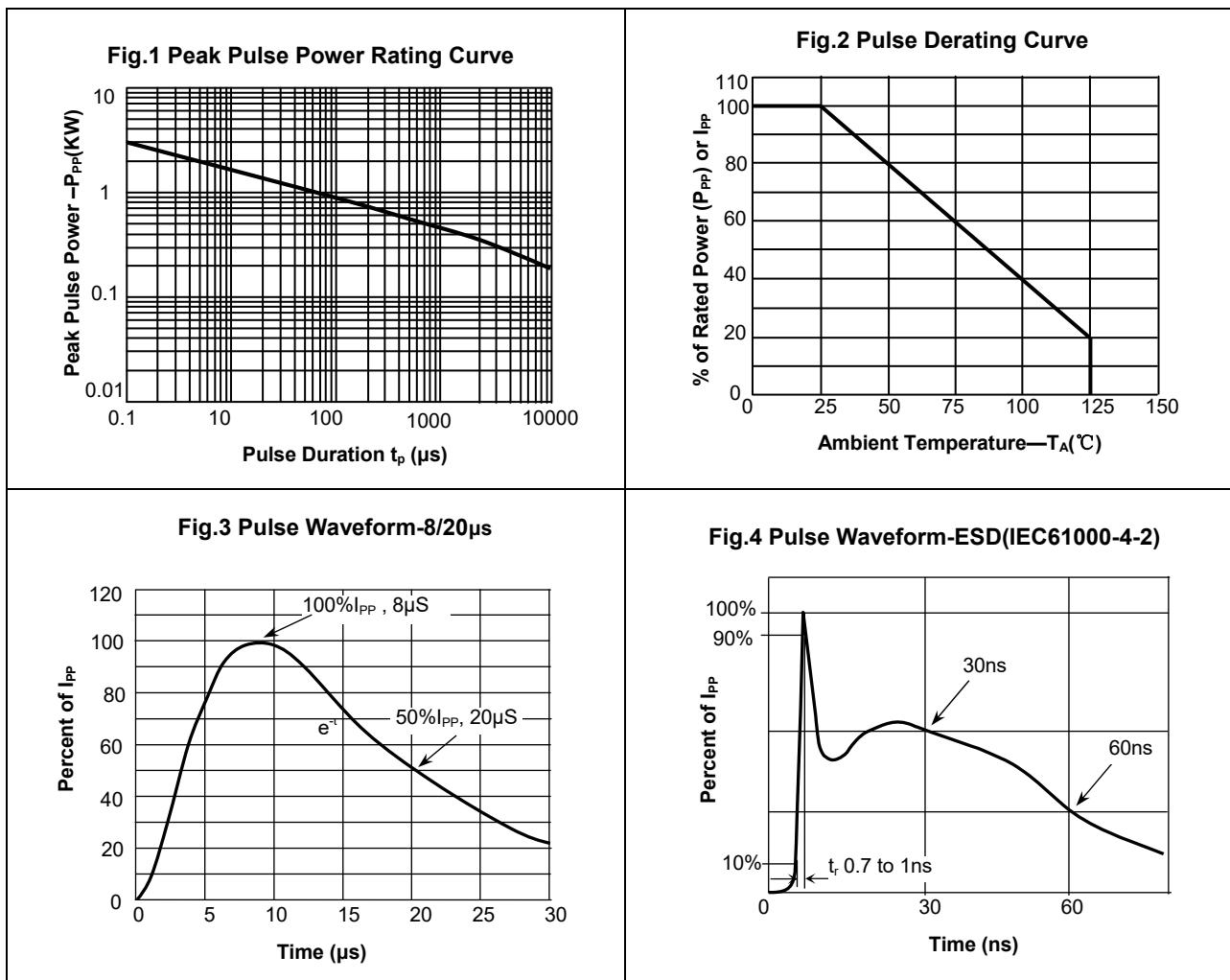
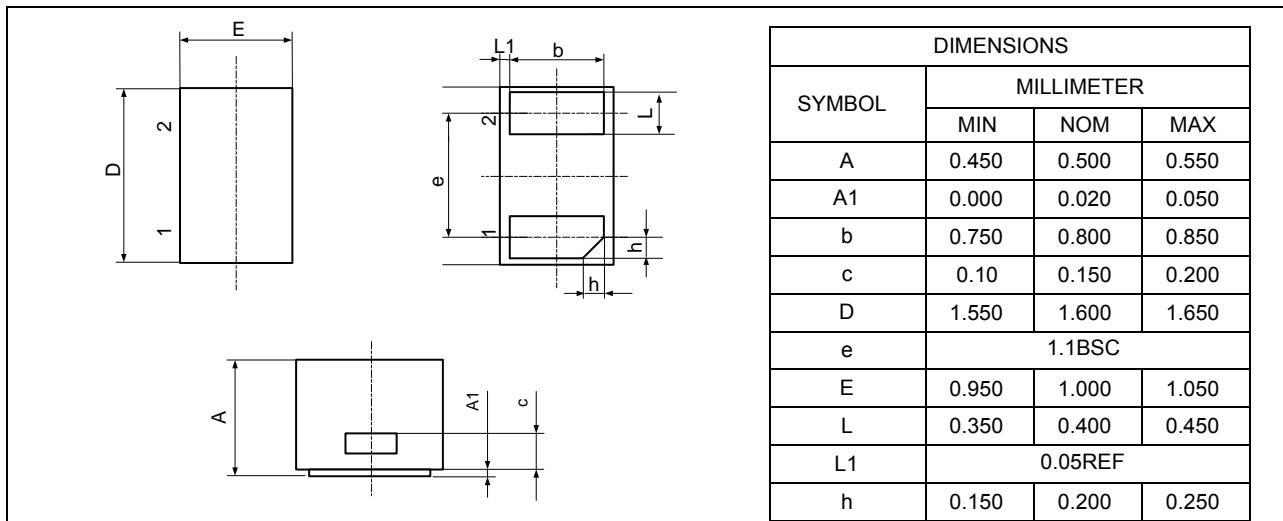
Ratings at 25 °C, ambient temperature unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Pulse Power ( $T_p=8/20\mu s$ )	P <sub>PP</sub>	1500	W
ESD contact/air discharge (IEC-61000-4-2)	V <sub>ESD</sub>	30/30	kV
Peak Pulse Current ( $T_p = 8/20\mu s$ )	I <sub>PP</sub>	52	A
Junction Temperature	T <sub>J</sub>	-55 to +150	°C
Storage temperature	T <sub>STG</sub>	-55 to +150	°C

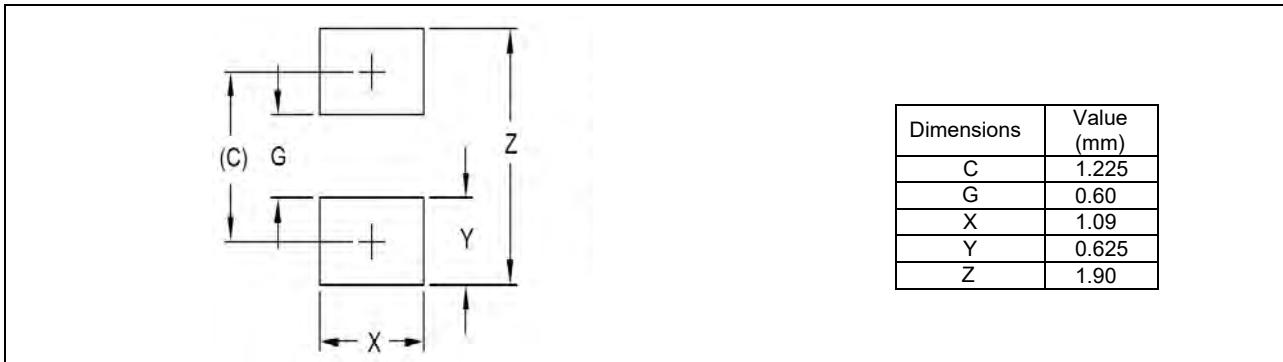
## Electrical Characteristics

(T<sub>A</sub> = 25 °C unless otherwise specified)

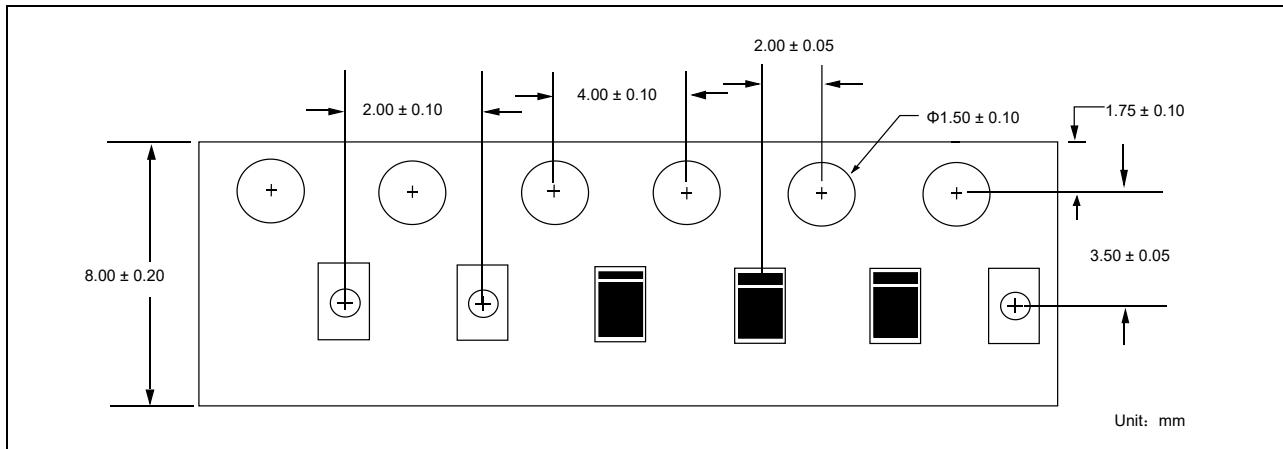
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V <sub>RWM</sub>				20	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA	22			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =20V			0.5	uA
Clamping Voltage (IEC 61000-4-5)	V <sub>C</sub>	I <sub>PP</sub> =10A, T <sub>p</sub> =8/20us		20		V
Clamping Voltage (IEC 61000-4-5)	V <sub>C</sub>	I <sub>PP</sub> =30A, T <sub>p</sub> =8/20us		25		V
Clamping Voltage (IEC 61000-4-5)	V <sub>C</sub>	I <sub>PP</sub> =52A, T <sub>p</sub> =8/20us		29		V
Clamping Voltage (TLP)	V <sub>C</sub>	I <sub>TLP</sub> =30A, T <sub>p</sub> =100ns		25		V
Dynamic Resistance	R <sub>DNY</sub>	T <sub>p</sub> =100ns		0.1		Ω
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> =0V, f=1MHz		70		pF

**Typical Characteristics** ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified)

**Package Dimensions**


### Pad Dimensions



### Package Information



### Marking



### Ordering information

Order code	Package	Packaging option	Base quantity	Weight	Packaging specification
YED16C22052AV	DFN1610-2	Tape and reel	100000pcs / reel	3.5mg	EIA STD RS-481